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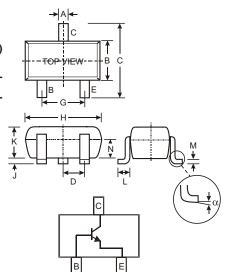
## NPN SMALL SIGNAL SURFACE MOUNT TRANSISTOR

#### **Features**

- Epitaxial Planar Die Construction
- Complementary PNP Type Available (MMBT3906T)
- Ultra-Small Surface Mount Package
- Available in Lead Free/RoHS Compliant Version (Note 2)

### **Mechanical Data**

- Case: SOT-523
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Solderable per MIL-STD-202, Method 208
- Also Available in Lead Free Plating (Matte Tin Finish annealed over Alloy 42 leadframe). Please see Ordering Information, Note 5, on Page 2
- Terminal Connections: See Diagram
- Marking (See Page 2): 1N
- Ordering & Date Code Information, See Page 2
- Weight: 0.002 grams (approximate)



SOT-523											
Dim	Min	Max	Тур								
Α	0.15	0.30	0.22								
В	0.75	0.85	0.80								
С	1.45	1.75	1.60								
D			0.50								
G	0.90	1.10	1.00								
Н	1.50	1.70	1.60								
J	0.00	0.10	0.05								
K	0.60	0.80	0.75								
L	0.10	0.30	0.22								
M	0.10	0.20	0.12								
N	0.45	0.65	0.50								
α	0°	8°									
AII D	imens	All Dimensions in mm									

## **Maximum Ratings** @ T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit	
Collector-Base Voltage	V <sub>CBO</sub>	60	V	
Collector-Emitter Voltage	V <sub>CEO</sub>	40	V	
Emitter-Base Voltage	V <sub>EBO</sub>	6.0	V	
Collector Current - Continuous	I <sub>C</sub>	200	mA	
Power Dissipation (Note 1)	P <sub>d</sub>	150	mW	
Thermal Resistance, Junction to Ambient (Note 1)	R <sub>0</sub> JA	833	°C/W	
Operating and Storage and Temperature Range	T <sub>j</sub> , T <sub>STG</sub>	-55 to +150	°C	

Notes: 1. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.

2. No purposefully added lead.



# Electrical Characteristics @ T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Symbol Min Ma		Unit	Test Condition			
OFF CHARACTERISTICS (Note 3)								
Collector-Base Breakdown Voltage		60	_	V	$I_C = 10\mu A, I_E = 0$			
Collector-Emitter Breakdown Voltage	V <sub>(BR)CEO</sub>	40	_	V	I <sub>C</sub> = 1.0mA, I <sub>B</sub> = 0			
Emitter-Base Breakdown Voltage	V <sub>(BR)EBO</sub>	6.0	_	V	$I_E = 10 \mu A, I_C = 0$			
Collector Cutoff Current	I <sub>CEX</sub>	_	50	nA	$V_{CE} = 30V, V_{EB(OFF)} = 3.0V$			
Base Cutoff Current	I <sub>BL</sub>	_	50	nA	$V_{CE} = 30V, V_{EB(OFF)} = 3.0V$			
ON CHARACTERISTICS (Note 3)			•	•				
DC Current Gain	h <sub>FE</sub>	40 70 100 60 30	300 —	_	$\begin{array}{c} I_{C} = 100\mu\text{A},  V_{CE} = 1.0\text{V} \\ I_{C} = 1.0\text{mA},  V_{CE} = 1.0\text{V} \\ I_{C} = 10\text{mA},  V_{CE} = 1.0\text{V} \\ I_{C} = 50\text{mA},  V_{CE} = 1.0\text{V} \\ I_{C} = 100\text{mA},  V_{CE} = 1.0\text{V} \\ \end{array}$			
Collector-Emitter Saturation Voltage	V <sub>CE(SAT)</sub>	_	0.20 0.30	V	I <sub>C</sub> = 10mA, I <sub>B</sub> = 1.0mA I <sub>C</sub> = 50mA, I <sub>B</sub> = 5.0mA			
Base- Emitter Saturation Voltage		0.65	0.85 0.95	V	I <sub>C</sub> = 10mA, I <sub>B</sub> = 1.0mA I <sub>C</sub> = 50mA, I <sub>B</sub> = 5.0mA			
SMALL SIGNAL CHARACTERISTICS								
Output Capacitance	Cobo	_	4.0	pF	$V_{CB} = 5.0V$ , $f = 1.0MHz$ , $I_E = 0$			
Input Capacitance	C <sub>ibo</sub>	_	8.0	pF	$V_{EB} = 0.5V$ , $f = 1.0MHz$ , $I_{C} = 0$			
Input Impedance	h <sub>ie</sub>	1.0	10	kΩ				
Voltage Feedback Ratio	h <sub>re</sub>	0.5	8.0	x 10 <sup>-4</sup>	$V_{CE} = 10V, I_{C} = 1.0mA,$			
Small Signal Current Gain	h <sub>fe</sub>	100	400	_	f = 1.0kHz			
Output Admittance	h <sub>oe</sub>	1.0	40	μS				
Current Gain-Bandwidth Product	f⊤	300	_	MHz	$V_{CE} = 20V$ , $I_C = 10mA$ , $f = 100MHz$			
Noise Figure	NF	_	5.0	dB	$V_{CE}$ = 5.0Vdc, $I_{C}$ = 100 $\mu$ Adc, $R_{S}$ = 1.0K $\Omega$ , $f$ = 1.0MHz			
SWITCHING CHARACTERISTICS								
Delay Time	t <sub>d</sub>	_	35	ns	V <sub>CC</sub> = 3.0V, I <sub>C</sub> = 10mA,			
Rise Time	t <sub>r</sub>	_	35	ns	$V_{BE(off)} = -0.5V, I_{B1} = 1.0mA$			
Storage Time	ts	_	200	ns	V <sub>CC</sub> = 3.0V, I <sub>C</sub> = 10mA			
Fall Time	t <sub>f</sub>	_	50	ns	$I_{B1} = I_{B2} = 1.0 \text{mA}$			

# **Ordering Information** (Note 4)

Device	Packaging	Shipping		
MMBT3904T-7	SOT-523	3000/Tape & Reel		

Notes: 3. Short duration test pulse used to minimize self-heating effect.

- 4. For Packaging Details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.
- 5. For Lead Free/RoHS Compliant version part number, please add "-F" suffix to the part number above. Example: MMBT3904T-7-F.

# **Marking Information**



1N = Product Type Marking Code YM = Date Code Marking

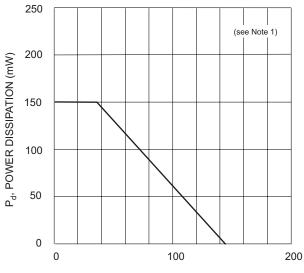
Y = Year (ex: N = 2002) M = Month (ex: 9 = September)

#### Date Code Key

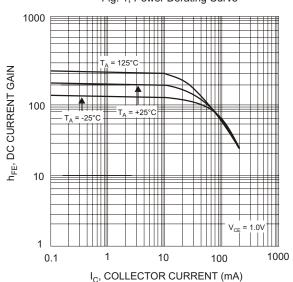
Year	2002	2003	2004	2005	2006	2007	2008	2009
Code	N	Р	R	S	Т	U	V	W

Month	Jan	Feb	March	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

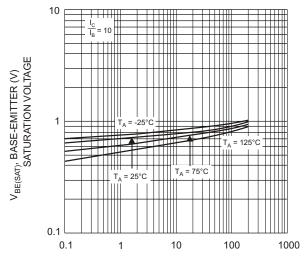




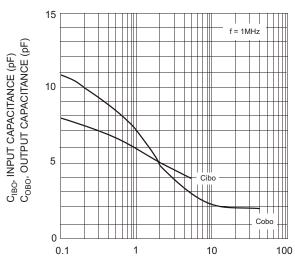
T<sub>A</sub>, AMBIENT TEMPERATURE (°C) Fig. 1, Power Derating Curve



I<sub>C</sub>, COLLECTOR CURRENT (mA) Fig. 3, Typical DC Current Gain vs Collector Current



I<sub>C</sub>, COLLECTOR CURRENT (mA) Fig. 5, Typical Base-Emitter Saturation Voltage vs. Collector Current



V<sub>CB</sub>, COLLECTOR-BASE VOLTAGE (V) Fig. 2, Input and Output Capacitance vs. Collector-Base Voltage

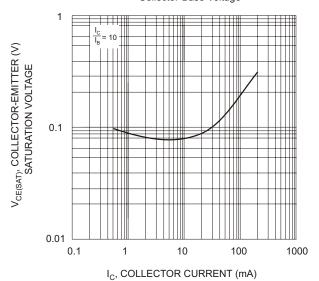


Fig. 4, Typical Collector-Emitter Saturation Voltage vs. Collector Current